

## N-Channel 250-V (D-S) MOSFET

PRODUCT SUMMARY		
V <sub>DS</sub> (V)	R <sub>rDS(on)</sub> (Ω)	I <sub>D</sub> (A)
250	0.155 at V <sub>GS</sub> = 10 V	3.0
	0.162 at V <sub>GS</sub> = 6.0 V	2.9

### FEATURES

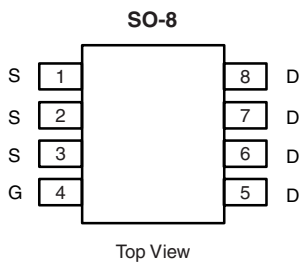
- Halogen-free According to IEC 61249-2-21 Definition
- PWM-Optimized TrenchFET® Power MOSFET
- 100 % R<sub>g</sub> Tested
- Avalanche Tested



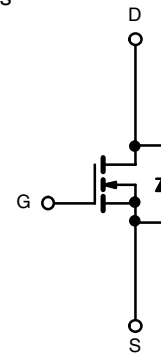
**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
Available

### APPLICATIONS

- Primary Side Switch In:
  - Telecom Power Supplies
  - Distributed Power Architectures
  - Miniature Power Modules



Ordering Information: Si4434DY-T1-E3 (Lead (Pb)-free)  
Si4434DY-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted				
Parameter	Symbol	10 s	Steady State	Unit
Drain-Source Voltage	V <sub>DS</sub>	250		V
Gate-Source Voltage	V <sub>GS</sub>	± 20		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	I <sub>D</sub>	T <sub>A</sub> = 25 °C	3.0	2.1
		T <sub>A</sub> = 70 °C	2.4	1.7
Pulsed Drain Current	I <sub>DM</sub>	30		A
Continuous Source Current (Diode Conduction) <sup>a</sup>	I <sub>S</sub>	2.6	1.3	
Avalanche Current	I <sub>AS</sub>	13		
Single Pulse Avalanche Energy	E <sub>AS</sub>	8.4		mJ
Maximum Power Dissipation <sup>a</sup>	P <sub>D</sub>	T <sub>A</sub> = 25 °C	3.1	1.56
		T <sub>A</sub> = 70 °C	2.0	1.0
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	R <sub>thJA</sub>	t ≤ 10 s	33	40
		Steady State	65	80
Maximum Junction-to-Foot (Drain)	R <sub>thJF</sub>	17	21	°C/W

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

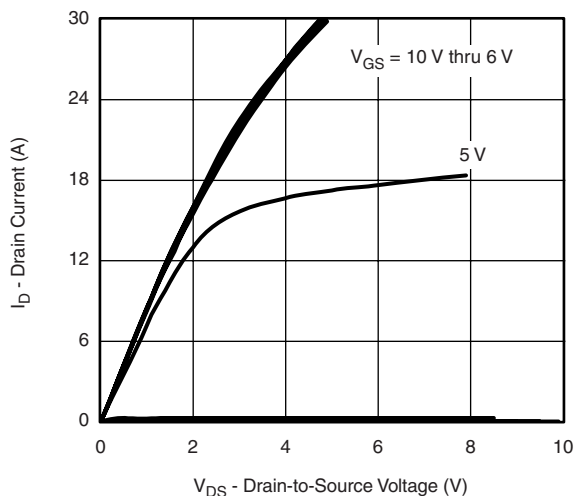
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$ , unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
<b>Static</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0		4.0	V
Gate-Body Leakage	$I_{GSS}$	$V_{DS} = 0\text{ V}, V_{GS} = \pm 20\text{ V}$			$\pm 100$	nA
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS} = 250\text{ V}, V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
		$V_{DS} = 250\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			15	
On-State Drain Current <sup>a</sup>	$I_{D(on)}$	$V_{DS} \geq 10\text{ V}, V_{GS} = 10\text{ V}$	20			A
Drain-Source On-State Resistance <sup>a</sup>	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 3.0\text{ A}$		0.129	0.155	$\Omega$
		$V_{GS} = 6.0\text{ V}, I_D = 2.9\text{ A}$		0.131	0.162	
Forward Transconductance <sup>a</sup>	$g_{fs}$	$V_{DS} = 15\text{ V}, I_D = 3.0\text{ A}$		14		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	$I_S = 2.8\text{ A}, V_{GS} = 0\text{ V}$		0.75	1.2	V
<b>Dynamic<sup>b</sup></b>						
Total Gate Charge	$Q_g$	$V_{DS} = 100\text{ V}, V_{GS} = 10\text{ V}, I_D = 3.0\text{ A}$		34	50	nC
Gate-Source Charge	$Q_{gs}$			6.8		
Gate-Drain Charge	$Q_{gd}$			10.5		
Gate Resistance	$R_g$		0.6	1.2	1.8	$\Omega$
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 100\text{ V}, R_L = 25\text{ }\Omega$ $I_D \cong 4.0\text{ A}, V_{GEN} = 10\text{ V}, R_g = 6\text{ }\Omega$		16	25	ns
Rise Time	$t_r$			23	35	
Turn-Off Delay Time	$t_{d(off)}$			47	70	
Fall Time	$t_f$			19	30	
Source-Drain Reverse Recovery Time	$t_{rr}$	$I_F = 2.8\text{ A}, di/dt = 100\text{ A}/\mu\text{s}$		100	150	

Notes:

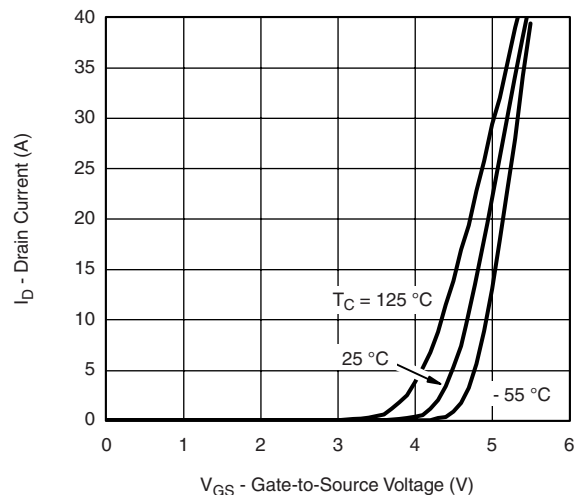
- a. Pulse test; pulse width  $\leq 300\text{ }\mu\text{s}$ , duty cycle  $\leq 2\%$ .
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

**TYPICAL CHARACTERISTICS**  $25\text{ }^\circ\text{C}$ , unless otherwise noted

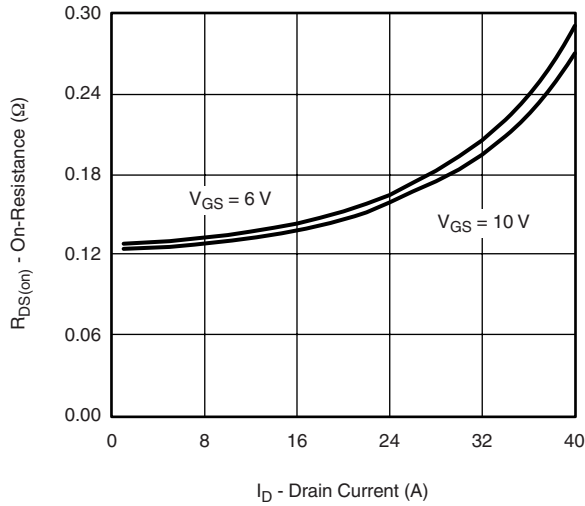


Output Characteristics

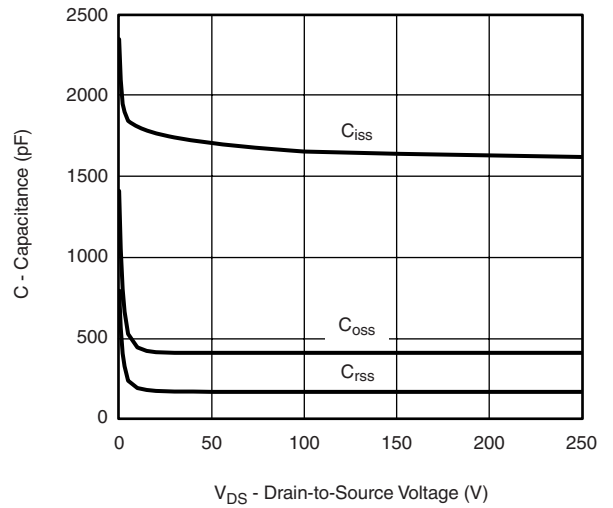


Transfer Characteristics

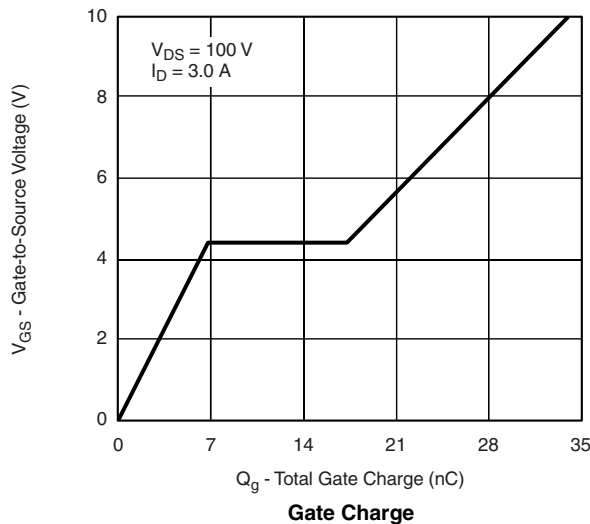
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



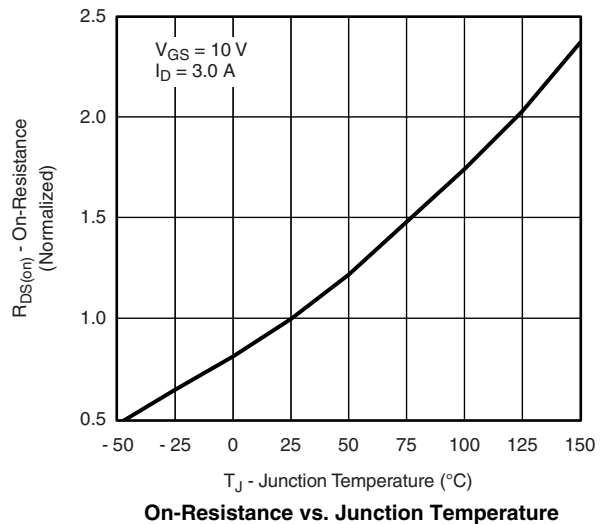
**On-Resistance vs. Drain Current**



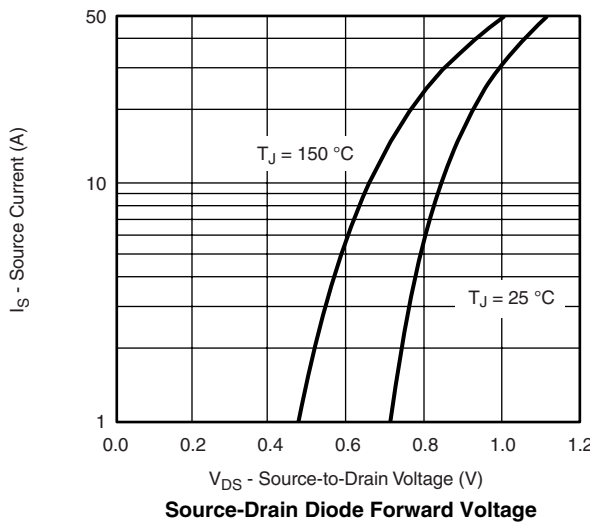
**Capacitance**



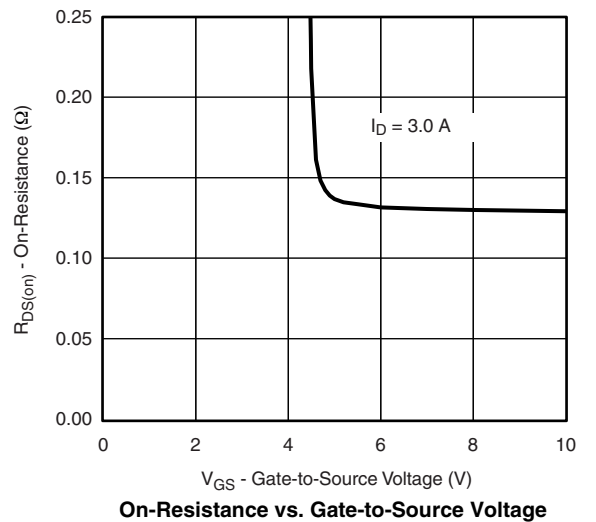
**Gate Charge**



**On-Resistance vs. Junction Temperature**

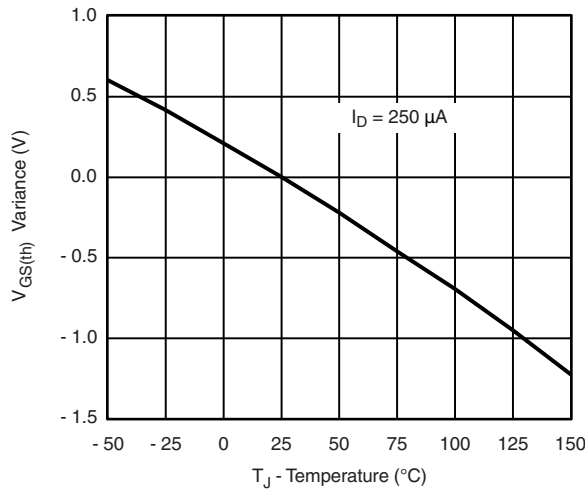


**Source-Drain Diode Forward Voltage**

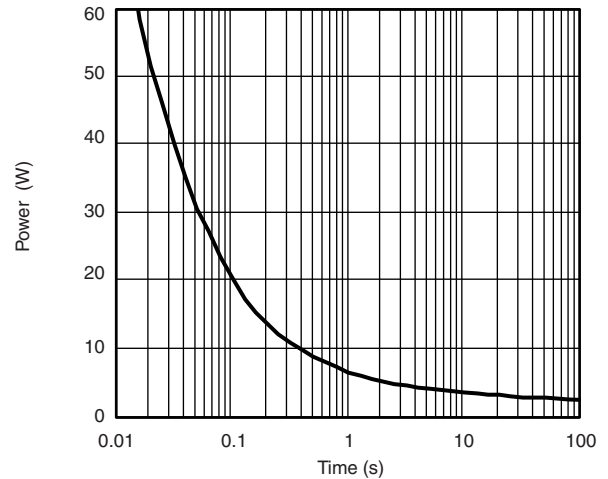


**On-Resistance vs. Gate-to-Source Voltage**

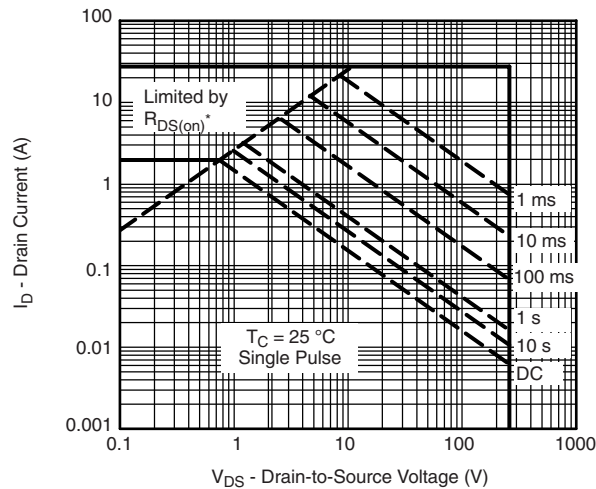
### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



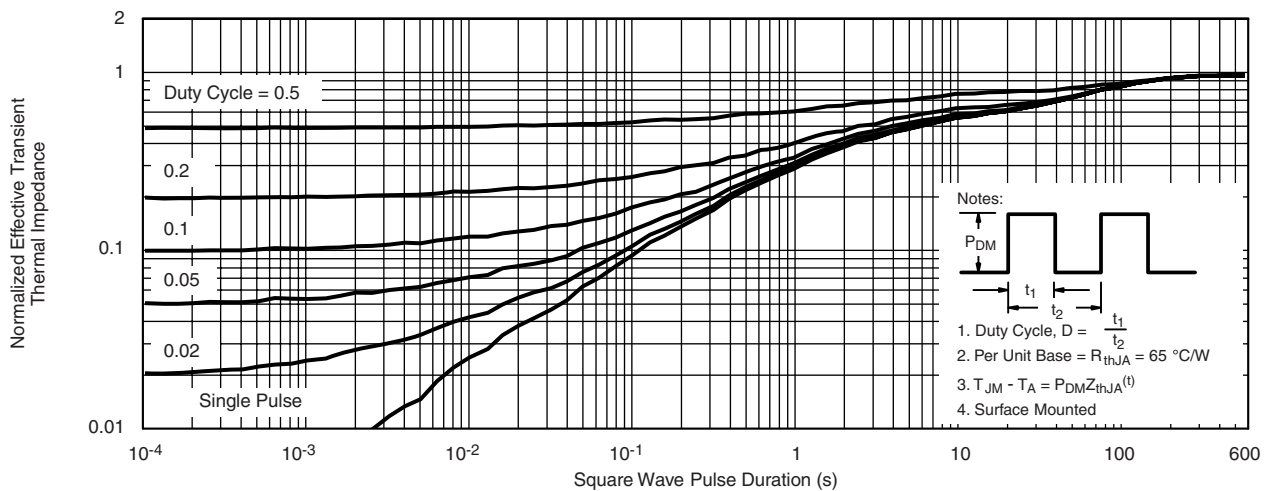
**Threshold Voltage**



**Single Pulse Power**



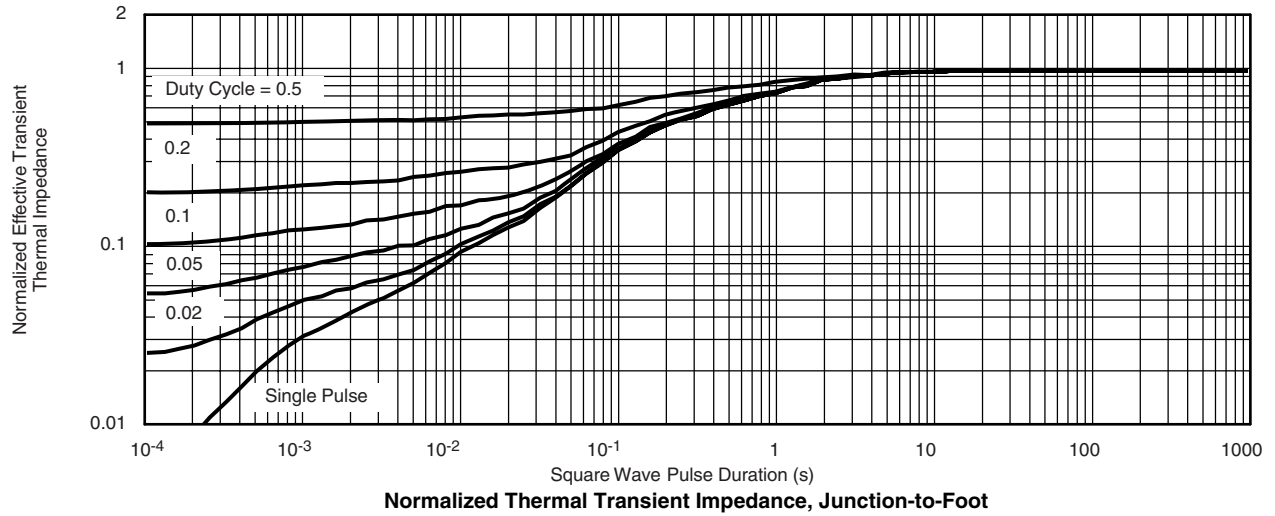
\*  $V_{GS} >$  minimum  $V_{GS}$  at which  $R_{DS(on)}$  is specified  
**Safe Operating Area, Junction-to-Case**



**Normalized Thermal Transient Impedance, Junction-to-Ambient**



**TYPICAL CHARACTERISTICS** 25 °C, unless otherwise noted



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## SOIC (NARROW): 8-LEAD

JEDEC Part Number: MS-012



DIM	MILLIMETERS		INCHES	
	Min	Max	Min	Max
A	1.35	1.75	0.053	0.069
A <sub>1</sub>	0.10	0.20	0.004	0.008
B	0.35	0.51	0.014	0.020
C	0.19	0.25	0.0075	0.010
D	4.80	5.00	0.189	0.196
E	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
H	5.80	6.20	0.228	0.244
h	0.25	0.50	0.010	0.020
L	0.50	0.93	0.020	0.037
q	0°	8°	0°	8°
S	0.44	0.64	0.018	0.026
ECN: C-06527-Rev. I, 11-Sep-06				
DWG: 5498				

## RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads  
Dimensions in Inches/(mm)

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